# STB300NH02L
# STP300NH02L

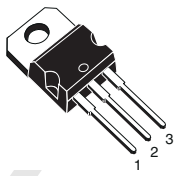
## N-channel 24V - 120A - TO-220 / D$^2$PAK
## STripFET™ Power MOSFET

**PRELIMINARY DATA**

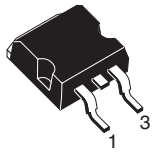
## General features

| Type | $V_{DSS}$ | $R_{DS(on)}$ | $I_D$ |
|---|---|---|---|
| STB300NH02L | 24V | < 1.8mΩ | 120A |
| STP300NH02L | 24V | < 2.2mΩ | 120A |

- $R_{DS(on)}$*$Q_g$ industry's benchmark
- Conduction losses reduced
- Switching losses reduced
- Low profile, very low parasitic inductance




TO-220

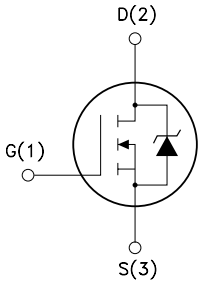



D²PAK

## Description

This product utilizes the latest advanced design rules of ST's proprietary STripFET™ technology. This is suitable for high current OR-ing application.

## Internal schematic diagram




## Applications

- Switching application
  - Specifically designed and optimized for high efficiency DC/DC converters
  - OR-ing

## Order codes

| Part number | Marking | Package | Packaging |
|---|---|---|---|
| STP300NH02L | P300NH02L | TO-220 | Tube |
| STB300NH02L | B300NH02L | D²PAK | Tape & reel |

DRAFT



This is preliminary information on a new product now in development or undergoing evaluation. Details are subject to change without notice.

www.st.com

# Contents

1 Electrical ratings . . . . . 3

2 Electrical characteristics . . . . . 4

2.1 Electrical characteristics (curves) . . . . . 6

3 Test circuit . . . . . 8

4 Package mechanical data . . . . . 9

5 Packaging mechanical data . . . . . 12

6 Revision history . . . . . 13

DRAFT

# 1 Electrical ratings

**Table 1. Absolute maximum ratings**

| Symbol | Parameter | Value | Unit |
|---|---|---|---|
| $V_{DS}$ | Drain-source voltage ($V_{GS}$ = 0) | 24 | V |
| $V_{GS}$ | Gate-source voltage | ± 20 | V |
| $I_D$ (1) | Drain current (continuous) at $T_C$ = 25°C | 120 | A |
| $I_D$ (1) | Drain current (continuous) at $T_C$ = 100°C | 120 | A |
| $I_{DM}$ (2) | Drain current (pulsed) | 480 | A |
| $P_{TOT}$ (3) | Total dissipation at $T_C$ = 25°C | 300 | W |
| | Derating factor | 2 | W/°C |
| $T_j$ | Operating junction temperature | -55 to 175 | °C |

1. This value is limited by package
2. Pulse width limited by safe operating area
3. This value is rated according Rthj-case

**Table 2. Thermal data**

| Symbol | Parameter | Value | Unit |
|---|---|---|---|
| Rthj-case | Thermal resistance junction-case max | 0.5 | °C/W |
| Rthj-amb | Thermal resistance junction-ambient max | 62.5 | °C/W |

**Table 3. Avalanche characteristics**

| Symbol | Parameter | Max value | Unit |
|---|---|---|---|
| $I_{AV}$ | Not-repetitive avalanche current (pulse width limited by Tj max) | 60 | A |
| $E_{AS}$ (1) | Single pulse avalanche energy | 2296 | J |

1. Starting Tj = 25°C, $I_D = I_{AV}$, $V_{DD}$ = 20V

DRAFT

# 2 Electrical characteristics

($T_{CASE}$=25°C unless otherwise specified)

**Table 4. On/off states**

| Symbol | Parameter | Test conditions | | Min. | Typ. | Max. | Unit |
|---|---|---|---|---|---|---|---|
| $V_{(BR)DSS}$ | Drain-source breakdown voltage | $I_D$ = 1mA, $V_{GS}$= 0 | | 24 | | | V |
| $I_{DSS}$ | Zero gate voltage drain current ($V_{GS}$ = 0) | $V_{DS}$ = 20V,<br>$V_{DS}$ = 20V, $T_c$=125°C | | | | 1<br>10 | µA<br>µA |
| $I_{GSS}$ | Gate body leakage current ($V_{DS}$ = 0) | $V_{DS}$ = ±20V | | | | ±100 | nA |
| $V_{GS(th)}$ | Gate threshold voltage | $V_{DS}$= $V_{GS}$, $I_D$ = 250µA | | 1 | | 2 | V |
| $R_{DS(on)}$ | Static drain-source on resistance | $V_{GS}$= 10V, $I_D$= 80A | TO-220<br>D²PAK | | 1.8<br>1.4 | 2.2<br>1.8 | mΩ<br>mΩ |
| $R_{DS(on)}$ | Static drain-source on resistance | $V_{GS}$= 10V, $I_D$= 80A @100°C | TO-220<br>D²PAK | | 2.7<br>2.1 | | mΩ<br>mΩ |

**Table 5. Dynamic**

| Symbol | Parameter | Test conditions | Min. | Typ. | Max. | Unit |
|---|---|---|---|---|---|---|
| $C_{iss}$<br>$C_{oss}$<br>$C_{rss}$ | Input capacitance<br>Output capacitance<br>Reverse transfer capacitance | $V_{DS}$ = 15V, f = 1 MHz, $V_{GS}$ =0 | | 7055<br>3251<br>307 | | pF<br>pF<br>pF |
| $Q_g$<br>$Q_{gs}$<br>$Q_{gd}$ | Total gate charge<br>Gate-source charge<br>Gate-drain charge | $V_{DD}$= 12V,$I_D$= 120A,<br>$V_{GS}$= 10V<br>*(see Figure 13)* | | 109.4<br>30.2<br>26.4 | | nC<br>nC<br>nC |
| $R_G$ | Gate input resistance | f=1 MHz Gate DC Bias = 0<br>Test signal level = 20mV<br>open drain | | 4.4 | | Ω |

DRAFT

**Table 6. Switching times**

| Symbol | Parameter | Test conditions | Min. | Typ. | Max. | Unit |
|---|---|---|---|---|---|---|
| $t_{d(on)}$<br>$t_r$ | Turn-on delay time<br>Rise time | $V_{DD}$ = 10V, $I_D$ = 60A<br>$R_G$= 4.7Ω, $V_{GS}$= 10V,<br>*(see Figure 12)* | | 18<br>275 | | ns<br>ns |
| $t_{d(off)}$<br>$t_f$ | Turn-off delay time<br>Fall time | $V_{DD}$ = 10V, $I_D$ = 60A<br>$R_G$= 4.7Ω, $V_{GS}$= 10V,<br>*(see Figure 12)* | | 138<br>94.4 | | ns<br>ns |

**Table 7. Source drain diode**

| Symbol | Parameter | Test conditions | Min | Typ. | Max | Unit |
|---|---|---|---|---|---|---|
| $I_{SD}$<br>$I_{SD}$ | Source-drain current<br>Source-drain current (pulsed) | | | | 120<br>640 | A<br>A |
| $V_{SD}$ (1) | Forward on voltage | $I_{SD}$ = 120 A, $V_{GS}$ = 0 | | | 1.3 | V |
| $t_{rr}$<br>$Q_{rr}$<br>$I_{RRM}$ | Reverse recovery time<br>Reverse recovery charge<br>Reverse recovery current | $I_{SD}$ = 120A, $V_{DD}$ = 20V,<br>di/dt = 100A/µs<br>$T_j$ = 25°C *(see Figure 17)* | | 63<br>85<br>2.7 | | ns<br>nC<br>A |
| $t_{rr}$<br>$Q_{rr}$<br>$I_{RRM}$ | Reverse recovery time<br>Reverse recovery charge<br>Reverse recovery current | $I_{SD}$ =120A, $V_{DD}$ = 20V<br>di/dt = 100A/µs<br>$T_j$ = 150°C *(see Figure 17)* | | 63.2<br>88<br>2.8 | | ns<br>nC<br>A |

1. Pulsed: pulse duration = 300µs, duty cycle 1.5%

DRAFT

## 2.1 Electrical characteristics (curves)

**Figure 1. Safe operating area**

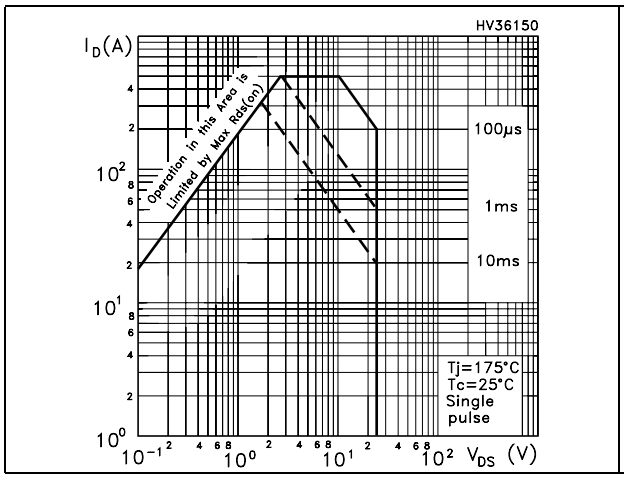



**Figure 2. Thermal impedance**

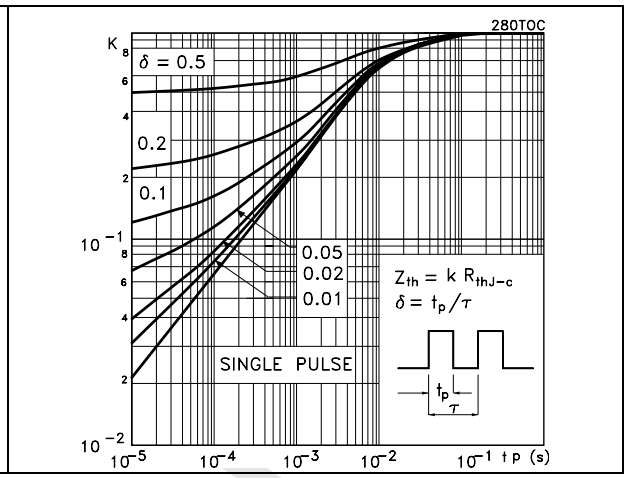



**Figure 3. Output characteristics**

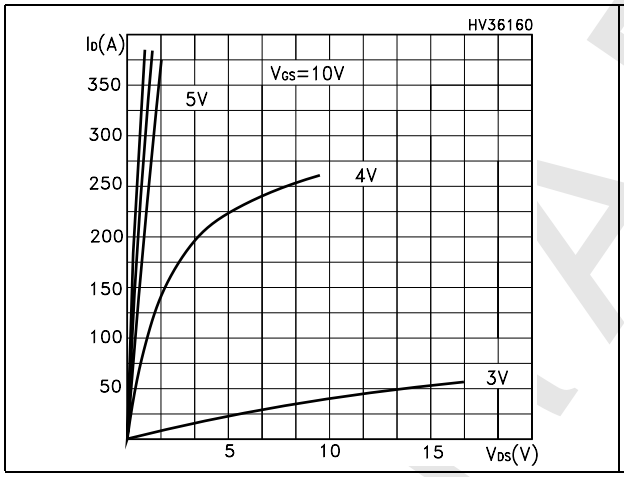



**Figure 4. Transfer characteristics**

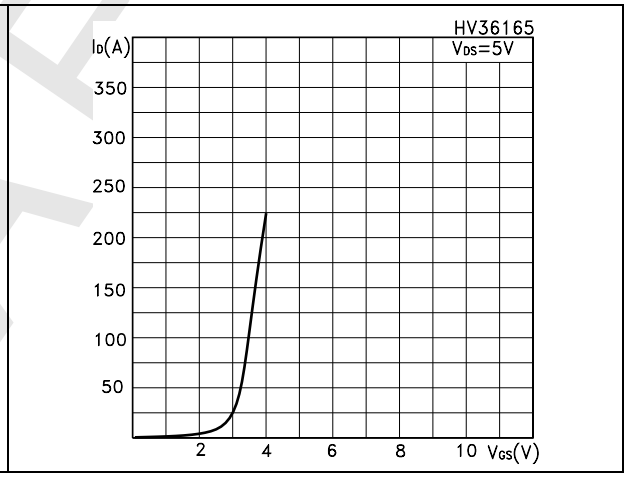



**Figure 5. Static drain-source on resistance**

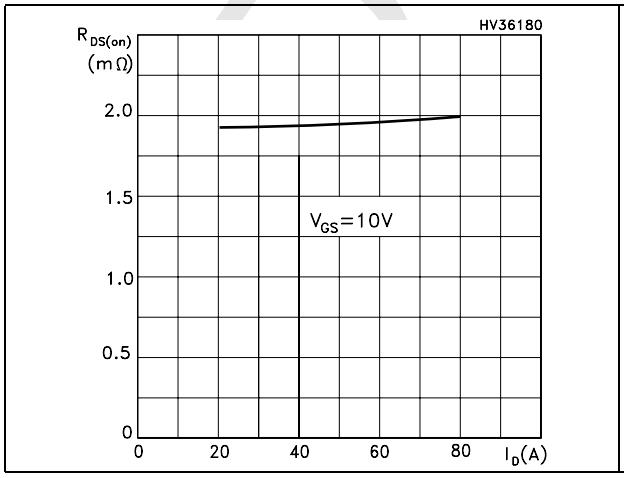



**Figure 6. Normalized $BV_{DSS}$ vs temperature**

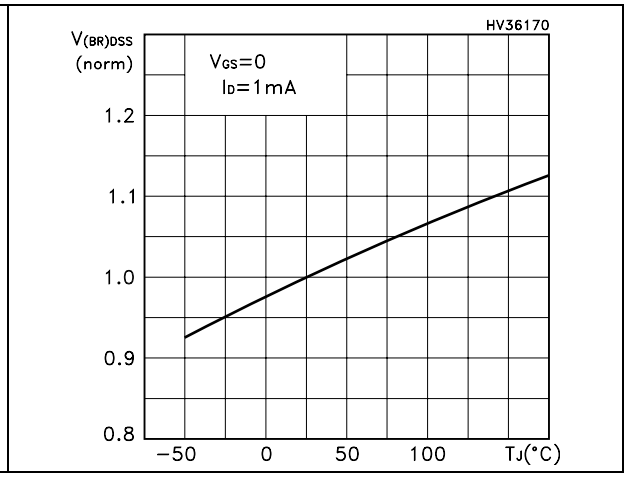


**Figure 7. Gate charge vs gate-source voltage**

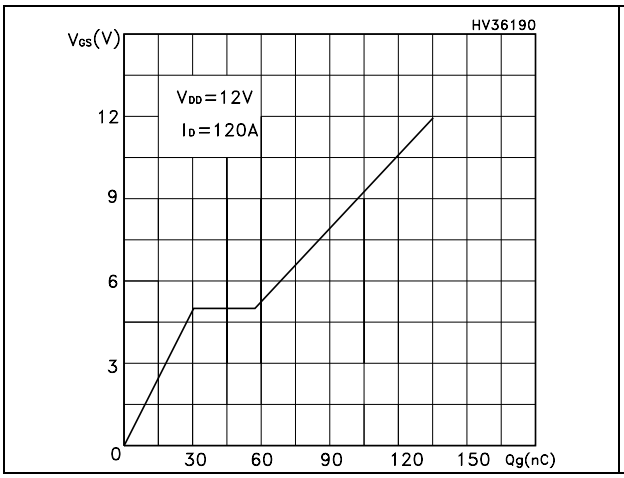



**Figure 8. Capacitance variations**

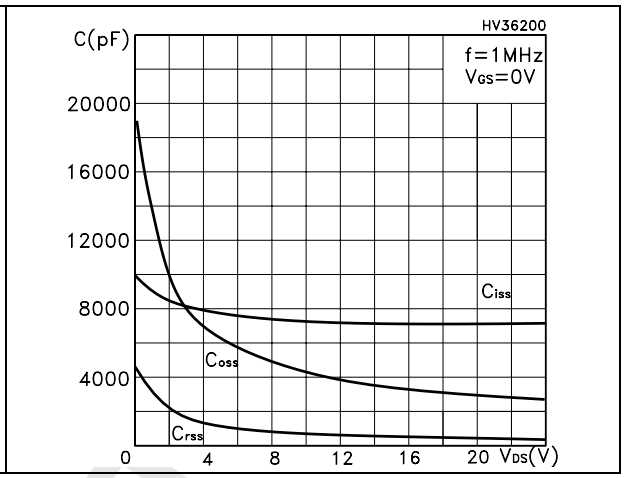



**Figure 9. Normalized gate threshold voltage vs temperature**

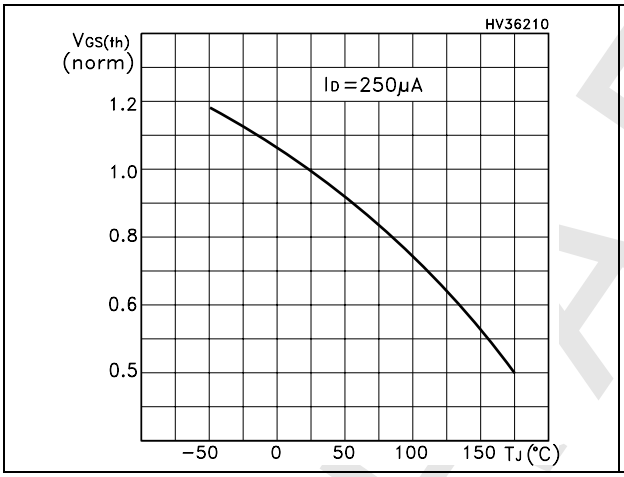



**Figure 10. Normalized on resistance vs temperature**

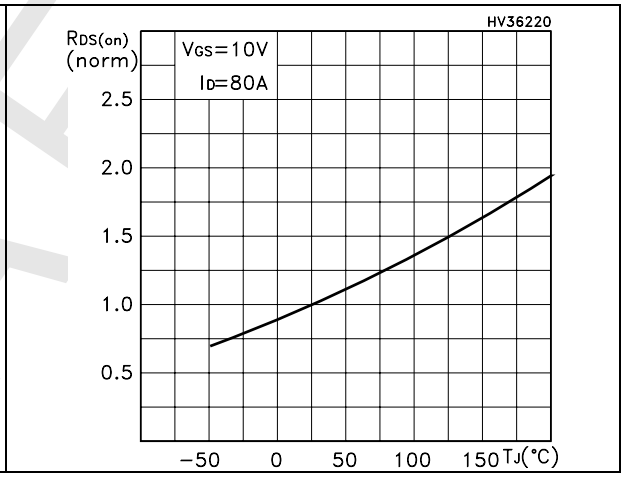
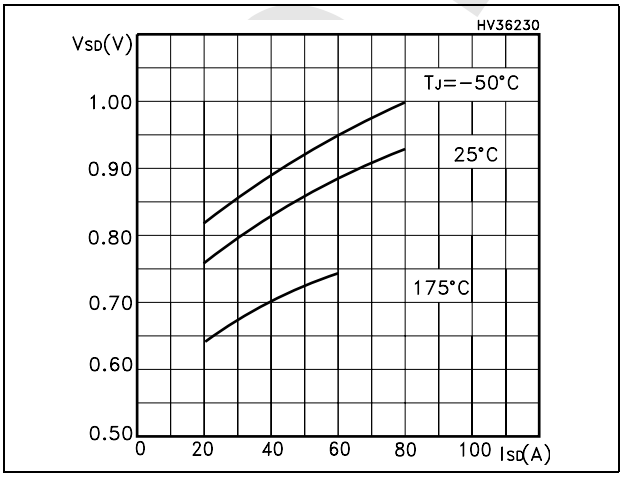



**Figure 11. Source-drain diode forward characteristics**



# 3 Test circuit

**Figure 12. Switching times test circuit for resistive load**

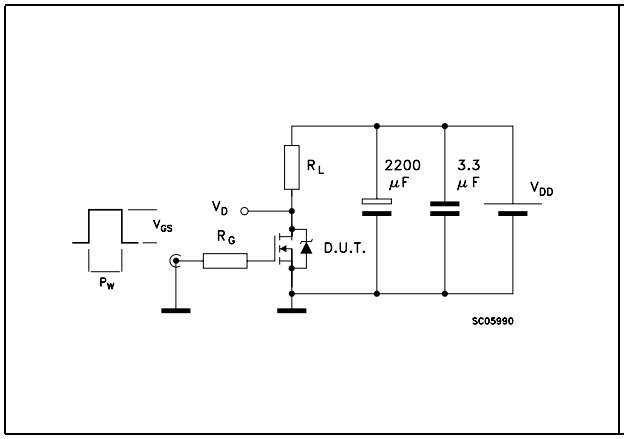



**Figure 13. Gate charge test circuit**

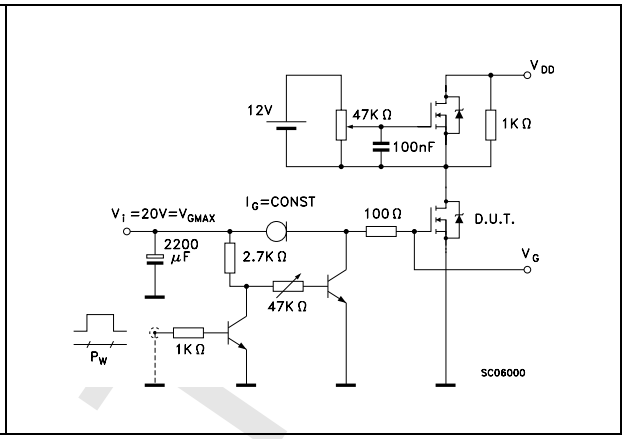



**Figure 14. Test circuit for inductive load switching and diode recovery times**

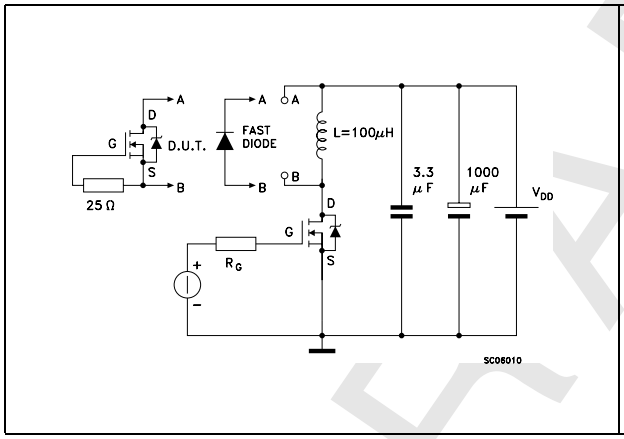



**Figure 15. Unclamped inductive load test circuit**

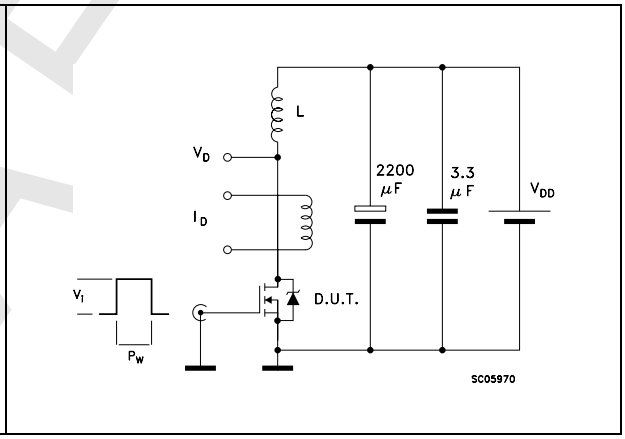



**Figure 16. Unclamped inductive waveform**

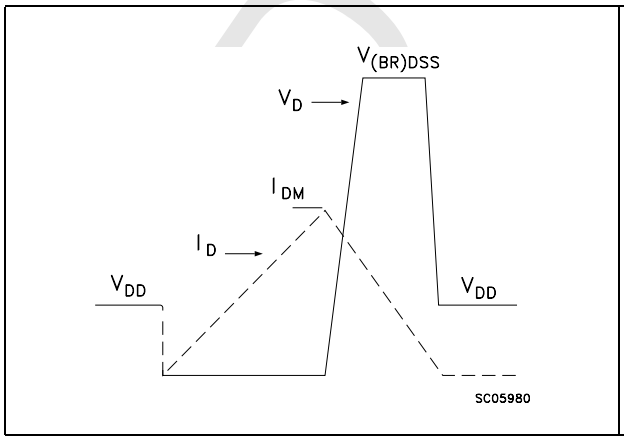
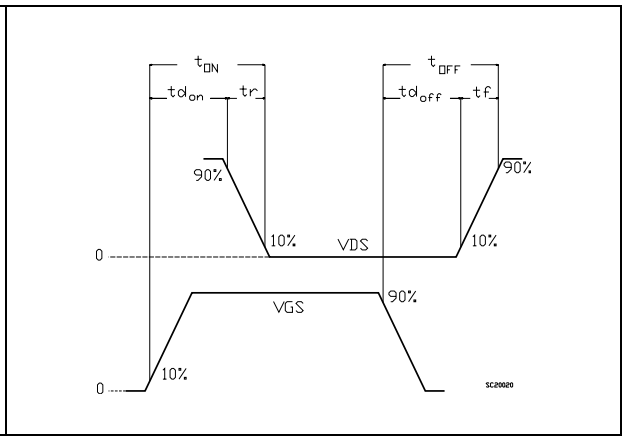



**Figure 17. Switching time waveform**




DRAFT

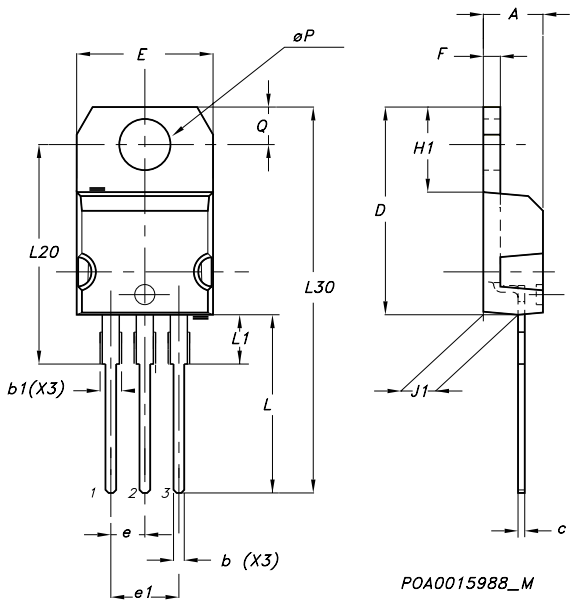
# 4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect. The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: *www.st.com*

DRAFT

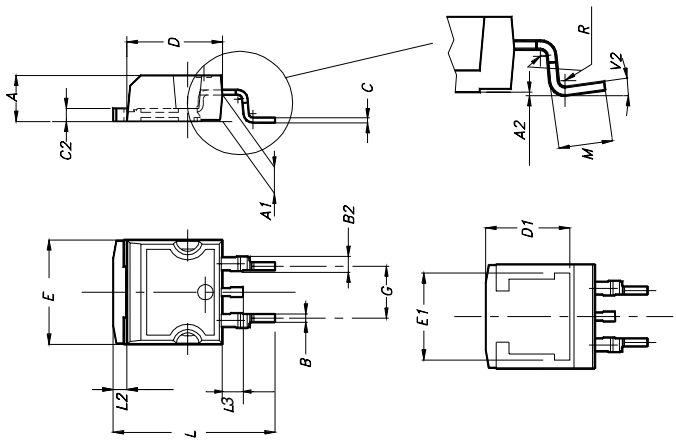
## TO-220 MECHANICAL DATA

| DIM. | mm. | | | inch | | |
|---|---|---|---|---|---|---|
| | MIN. | TYP | MAX. | MIN. | TYP. | MAX. |
| A | 4.40 | | 4.60 | 0.173 | | 0.181 |
| b | 0.61 | | 0.88 | 0.024 | | 0.034 |
| b1 | 1.15 | | 1.70 | 0.045 | | 0.066 |
| c | 0.49 | | 0.70 | 0.019 | | 0.027 |
| D | 15.25 | | 15.75 | 0.60 | | 0.620 |
| E | 10 | | 10.40 | 0.393 | | 0.409 |
| e | 2.40 | | 2.70 | 0.094 | | 0.106 |
| e1 | 4.95 | | 5.15 | 0.194 | | 0.202 |
| F | 1.23 | | 1.32 | 0.048 | | 0.052 |
| H1 | 6.20 | | 6.60 | 0.244 | | 0.256 |
| J1 | 2.40 | | 2.72 | 0.094 | | 0.107 |
| L | 13 | | 14 | 0.511 | | 0.551 |
| L1 | 3.50 | | 3.93 | 0.137 | | 0.154 |
| L20 | | 16.40 | | | 0.645 | |
| L30 | | 28.90 | | | 1.137 | |
| øP | 3.75 | | 3.85 | 0.147 | | 0.151 |
| Q | 2.65 | | 2.95 | 0.104 | | 0.116 |



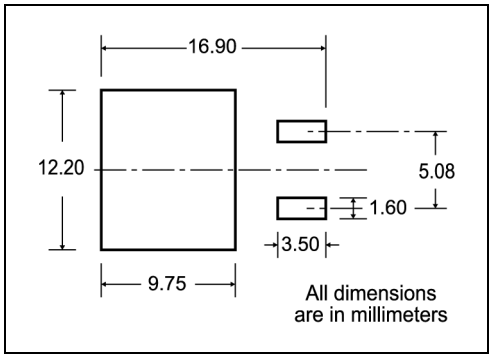
## D²PAK MECHANICAL DATA

| DIM. | mm. | | | inch | | |
|---|---|---|---|---|---|---|
| | MIN. | TYP | MAX. | MIN. | TYP. | MAX. |
| A | 4.4 | | 4.6 | 0.173 | | 0.181 |
| A1 | 2.49 | | 2.69 | 0.098 | | 0.106 |
| A2 | 0.03 | | 0.23 | 0.001 | | 0.009 |
| B | 0.7 | | 0.93 | 0.027 | | 0.036 |
| B2 | 1.14 | | 1.7 | 0.044 | | 0.067 |
| C | 0.45 | | 0.6 | 0.017 | | 0.023 |
| C2 | 1.23 | | 1.36 | 0.048 | | 0.053 |
| D | 8.95 | | 9.35 | 0.352 | | 0.368 |
| D1 | | 8 | | | 0.315 | |
| E | 10 | | 10.4 | 0.393 | | |
| E1 | | 8.5 | | | 0.334 | |
| G | 4.88 | | 5.28 | 0.192 | | 0.208 |
| L | 15 | | 15.85 | 0.590 | | 0.625 |
| L2 | 1.27 | | 1.4 | 0.050 | | 0.055 |
| L3 | 1.4 | | 1.75 | 0.055 | | 0.068 |
| M | 2.4 | | 3.2 | 0.094 | | 0.126 |
| R | | 0.4 | | | 0.015 | |
| V2 | 0º | | 4º | | | |

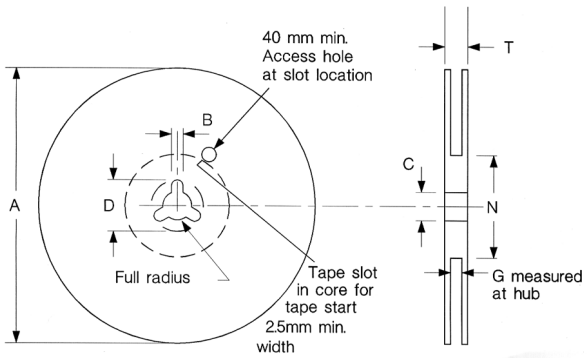


# 5 Packaging mechanical data

## D²PAK FOOTPRINT




## TAPE AND REEL SHIPMENT



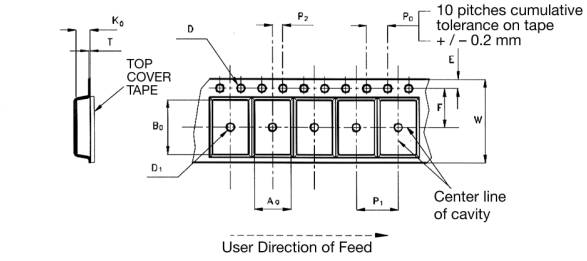

REEL MECHANICAL DATA

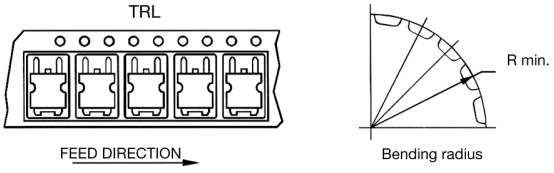
| DIM. | mm | | inch | |
|---|---|---|---|---|
| | MIN. | MAX. | MIN. | MAX. |
| A | | 330 | | 12.992 |
| B | 1.5 | | 0.059 | |
| C | 12.8 | 13.2 | 0.504 | 0.520 |
| D | 20.2 | | 0795 | |
| G | 24.4 | 26.4 | 0.960 | 1.039 |
| N | 100 | | 3.937 | |
| T | | 30.4 | | 1.197 |

| BASE QTY | BULK QTY |
|---|---|
| 1000 | 1000 |

TAPE MECHANICAL DATA

| DIM. | mm | | inch | |
|---|---|---|---|---|
| | MIN. | MAX. | MIN. | MAX. |
| A0 | 10.5 | 10.7 | 0.413 | 0.421 |
| B0 | 15.7 | 15.9 | 0.618 | 0.626 |
| D | 1.5 | 1.6 | 0.059 | 0.063 |
| D1 | 1.59 | 1.61 | 0.062 | 0.063 |
| E | 1.65 | 1.85 | 0.065 | 0.073 |
| F | 11.4 | 11.6 | 0.449 | 0.456 |
| K0 | 4.8 | 5.0 | 0.189 | 0.197 |
| P0 | 3.9 | 4.1 | 0.153 | 0.161 |
| P1 | 11.9 | 12.1 | 0.468 | 0.476 |
| P2 | 1.9 | 2.1 | 0.075 | 0.082 |
| R | 50 | | 1.574 | |
| T | 0.25 | 0.35 | 0.0098 | 0.0137 |
| W | 23.7 | 24.3 | 0.933 | 0.956 |




* on sales type

# 6 Revision history

Table 8. Revision history

| Date | Revision | Changes |
|---|---|---|
| 21-Feb-2007 | 1 | First release |

DRAFT

**Please Read Carefully:**

Information in this document is provided solely in connection with ST products. STMicroelectronics NV and its subsidiaries (“ST”) reserve the right to make changes, corrections, modifications or improvements, to this document, and the products and services described herein at any time, without notice.

All ST products are sold pursuant to ST’s terms and conditions of sale.

Purchasers are solely responsible for the choice, selection and use of the ST products and services described herein, and ST assumes no liability whatsoever relating to the choice, selection or use of the ST products and services described herein.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted under this document. If any part of this document refers to any third party products or services it shall not be deemed a license grant by ST for the use of such third party products or services, or any intellectual property contained therein or considered as a warranty covering the use in any manner whatsoever of such third party products or services or any intellectual property contained therein.

**UNLESS OTHERWISE SET FORTH IN ST’S TERMS AND CONDITIONS OF SALE ST DISCLAIMS ANY EXPRESS OR IMPLIED WARRANTY WITH RESPECT TO THE USE AND/OR SALE OF ST PRODUCTS INCLUDING WITHOUT LIMITATION IMPLIED WARRANTIES OF MERCHANTABILITY, FITNESS FOR A PARTICULAR PURPOSE (AND THEIR EQUIVALENTS UNDER THE LAWS OF ANY JURISDICTION), OR INFRINGEMENT OF ANY PATENT, COPYRIGHT OR OTHER INTELLECTUAL PROPERTY RIGHT.**

**UNLESS EXPRESSLY APPROVED IN WRITING BY AN AUTHORIZED ST REPRESENTATIVE, ST PRODUCTS ARE NOT RECOMMENDED, AUTHORIZED OR WARRANTED FOR USE IN MILITARY, AIR CRAFT, SPACE, LIFE SAVING, OR LIFE SUSTAINING APPLICATIONS, NOR IN PRODUCTS OR SYSTEMS WHERE FAILURE OR MALFUNCTION MAY RESULT IN PERSONAL INJURY, DEATH, OR SEVERE PROPERTY OR ENVIRONMENTAL DAMAGE. ST PRODUCTS WHICH ARE NOT SPECIFIED AS "AUTOMOTIVE GRADE" MAY ONLY BE USED IN AUTOMOTIVE APPLICATIONS AT USER’S OWN RISK.**

Resale of ST products with provisions different from the statements and/or technical features set forth in this document shall immediately void any warranty granted by ST for the ST product or service described herein and shall not create or extend in any manner whatsoever, any liability of ST.

ST and the ST logo are trademarks or registered trademarks of ST in various countries.

Information in this document supersedes and replaces all information previously supplied.

The ST logo is a registered trademark of STMicroelectronics. All other names are the property of their respective owners.

© 2007 STMicroelectronics - All rights reserved

STMicroelectronics group of companies

Australia - Belgium - Brazil - Canada - China - Czech Republic - Finland - France - Germany - Hong Kong - India - Israel - Italy - Japan - Malaysia - Malta - Morocco - Singapore - Spain - Sweden - Switzerland - United Kingdom - United States of America

**www.st.com**